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The Role of Metal-Nanotube Contact in the Performance of Carbon Nanotube Field-Effect Transistors: Survey Paper

Suchi C, Sinchana V Bhat, Tanuja C, Yashaswini M A

Department of Electronics and Communication Engineering,
Dayananda Sagar Academy of Technology and Management, Bangalore, Karnataka, India

ABSTRACT
Single-walled carbon nanotubes (SWNTs) have proven to be essential building blocks for nanoscale electronics owing to their outstanding electrical characteristics and quasi-one-dimensional geometry. The present research examines the electron-phonon interaction in metallic SWNTs, an important factor affecting charge transport behavior under varying bias conditions. With a new experimental technique where an atomic force microscope (AFM) tip was used as a mobile electrical contact, resistance was measured for different nanotube lengths and electrical biases. At low bias, the electron mean free path was determined to be about 1.6 µm, in agreement with weak acoustic phonon scattering. But at high bias, a sudden drop in the mean free path to about 10 nm was seen, caused by fast scattering by optical and zone-boundary phonons. Theoretical computations based on Boltzmann transport theory validate the experimental findings, providing quantitative information about current saturation and high-field transport behavior. These studies significantly further the knowledge of intrinsic transport limitations in SWNTs and recommend their use in high-performance nanoscale devices.

KEYWORDS: *Carbon Nanotube Field-Effect Transistors (CNFETs), Single-Walled Carbon Nanotubes (SWNTs), Metal–Nanotube Contact, Electron-Phonon Scattering, Ballistic Transport, Schottky Barrier, Contact Resistance, High-Bias Transport, Current Saturation, Boltzmann Transport Equation*

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INTRODUCTION

Wireless Body Area Networks (WBANs) have become a central technology in current healthcare systems, allowing for continuous monitoring of physiological parameters by wearable and implantable sensor nodes. WBANs form an essential part of improving patient care through real-time data collection and transmission to medical specialists without hindering daily life. Yet the strict energy requirements of WBAN nodes, owing to the short battery life and the imperative of sustained operation, pose serious challenges to MAC protocol development. This work suggests the design of an energy-efficient MAC protocol suited for WBANs and realized through FPGA technology. Taking advantage of the parallelism and reconfigurability of FPGAs, the design is expected to realize significant power savings while ensuring uninterrupted communication. The new protocol features a unique scheduling mechanism that reduces idle listening, collision, and overhearing—primary causes of energy expenditure in traditional MAC protocols. Through hardware implementation and simulation, this research assesses the performance of the suggested MAC protocol in extending node lifetime and facilitating energy-efficient data transmission in WBAN environments. The project emphasizes the significance of FPGA-based solutions in promoting low-power communication strategies for healthcare and biomedical applications.[1]

Single-wall carbon nanotubes (SWNTs) have captivated significant interest in the field of nanoscale electronics due to their unique one-dimensional structure and exceptional electrical properties. Metallic SWNTs, in particular, are predicted to exhibit quantized conductance with minimal resistance, making them ideal candidates for high-performance nanoscale devices. However, early experimental studies were often limited by high-resistance contacts that introduced tunneling barriers, dominating the transport characteristics and obscuring the intrinsic behavior of the nanotubes. A critical unresolved question in the study of SWNTs is the nature of electron transport under high electric fields: whether it remains ballistic or is influenced significantly by scattering mechanisms. While low-temperature studies have suggested long mean free paths due to suppressed backscattering, the behavior of high-energy electrons under strong bias has remained largely unexplored. This work presents a detailed investigation of the intrinsic high-field transport properties of metallic SWNTs using low-resistance electrical contacts. The findings reveal that individual nanotubes can sustain current densities exceeding 10910^9109 A/cm². A dramatic decrease in conductance at high bias is observed, which is attributed to scattering by optical or zone-boundary phonons. A theoretical model incorporating elastic and inelastic scattering via the Boltzmann transport equation supports the experimental results, offering deep insights into current saturation phenomena in these systems. This study thus lays foundational understanding for the use of carbon nanotubes in high-current, high-speed electronic applications.[2]

Since conventional silicon-based transistor technology is reaching its physical and performance boundaries, new nanotechnologies like Carbon Nanotube Field Effect Transistors (CNFETs) have come up as potential contenders for the next-generation electronic components. CNFETs have distinct strengths such as increased carrier mobility, reduced power consumption, and enhanced electrostatic control over traditional CMOS devices. In view of the support required for the design and simulation of circuits utilizing this upcoming technology, the VS-CNFET 1.0.1 tool has been created. VS-CNFET (Virtuoso Spectre-CNFET) offers a strong simulation platform embedded within the Cadence Virtuoso environment, allowing researchers and engineers to model, analyze, and verify CNFET-based designs. VS-CNFET closes the gap between theoretical CNFET models and real-world circuit simulation, enabling innovation in nanoscale electronic design.[3]

Carbon nanotubes (CNTs), and in particular single-wall carbon nanotubes (SWNTs), have fascinating quasi-one-dimensional structures with outstanding electronic characteristics, for which reason they are extremely promising candidates for next-generation nano electronic devices. Their application in field-effect transistors (FETs) has drawn a lot of attention, yet first-generation devices were mostly unipolar, p-type devices with high contact resistance—due mainly to environmental doping and imperfect contact engineering. In contrast to traditional planar metal-semiconductor interfaces, these TiC-SWNT junctions exhibit low-resistance injection for both electron and hole carriers. The gate field successfully modulates the apparent Schottky barrier heights, allowing Ohmic-like behavior and stable ambipolar conduction. These results contradict the hypothesis that p-type character is inherent in s-SWNTs and emphasize the importance of electrostatics and contact geometry in controlling transport behavior. The study paves the way for future complementary logic and ambipolar device concepts in electronics based on CNTs.[4]

Li-passivation in zigzag GaN nanoribbons significantly modifies their electronic properties, enhancing Fermi velocity and reducing effective mass to improve carrier mobility. DFT investigations further show strong gas adsorption and charge transfer, highlighting their potential as high-performance nanosensors[5-6].

Carbon nanotubes (CNTs), because of their quasi-one-dimensionality and superior electronic behavior, have found themselves to be highly potential materials for nanoscale electronic devices. Their most notable applications include use in field-effect transistors (FETs), where semiconducting CNTs may be used as the channel whose conductivity can be controlled by an external electric field. Experiments have demonstrated that CNTs display p-type behavior even when there is no deliberate doping, and switching characteristics are strongly dependent upon contact properties, impurities, and environmental conditions. This paper reports a theoretical exploration of switching properties of semiconducting CNTs, especially the interaction of these CNTs with metal electrodes, and the role played by gate fields. Employing Green's function methods in the Landauer-Büttiker formalism, the authors investigate the influence of MIGS and assess limits to CNT-FET performance as the device channel is miniaturized. A central result is that CNT-FETs with 50 Å channel lengths are capable of possessing very good switching performance, with On/Off ratios well in excess of 10^4, and thereby supporting the possibility of severe miniaturization without loss of device function. These findings are essential for further developing ultra-small, high-speed, and low-power CNT transistors toward future nanoelectronics.[7] 5]

DFT-based studies demonstrate that Indium Nitride nanoribbons can effectively detect gases like CO, CO_2, NO, and NO_2 due to notable charge transfer and band structure modulation. Similarly, Scandium

Nitride monolayers show strong adsorption sensitivity toward toxic gases such as NH_3, AsH_3, BF_3, and BCl_3. Zigzag silicon carbide nanoribbons exhibit enhanced gas sensing performance through improved electronic response to hazardous gas molecules, making them promising for advanced sensor applications[8-10] 10-12].

Carbon nanotubes (CNTs), with their unique one-dimensional structure and exceptional electrical properties, have emerged as promising materials for future nanoscale electronics. Depending on their structure, CNTs can exhibit either metallic or semiconducting behavior, making them versatile components for molecular-scale devices. In this study, the fabrication and electrical performance of FETs based on individual single-wall and multi-wall carbon nanotubes (MWNTs) are examined. The SWNT-FETs demonstrate strong gate-dependent modulation of conductance—exceeding five orders of magnitude—indicating their effectiveness as p-type transistors dominated by hole transport. In contrast, pristine MWNTs typically show no gate effect due to their larger diameters and associated metallic behavior. However, the work also reveals that structural deformations, such as tube collapse, can significantly alter MWNT electronic properties, enabling FET-like behavior. This investigation provides insight into the charge transport mechanisms, carrier densities, and mobilities in CNT-based devices, affirming their suitability for next-generation nano electronic applications and highlighting the influence of structural and environmental factors on device operation.[11] 6]

Density Functional Theory (DFT) investigations reveal that Cu and Fe doping in boron nitride nanoribbons (BNNRs) significantly enhances their electrical conductivity, making them suitable candidates for nanoscale interconnects in advanced integrated circuits. Ab-initio studies on aluminum nitride nanoribbons (AlNNRs) demonstrate their potential in implementing reconfigurable logic gates due to tunable electronic properties under external stimuli. Additionally, the design of a FinFET-based operational amplifier (Op-Amp) using 22 nm high-k dielectric technology shows promising results in reducing leakage currents and enhancing performance, offering a robust solution for low-power, high-efficiency analog circuit applications[12-14] 14-16].

Carbon nanotubes (CNTs) are being considered potential ultra-scaled field-effect transistor (FET) candidates owing to their remarkable electrical characteristics and nanometer-sized dimensions. Whereas early models of CNT transistors (CNT-FETs) had drawn analogies with traditional FETs—hypothesizing channel modulation through gate control—experimental findings have increasingly indicated the pivotal nature of metal-nanotube contacts. More specifically, Schottky barriers (SBs) at such contacts have emerged as a determining factor in dictating device characteristics. This work develops a complete theoretical model showing CNT-FETs to behave mostly as Schottky barrier transistors, in which gate-controlled modulation of the contact resistance, and not the internal channel conductivity, controls switching behaviors. Through self-consistent electrostatic calculations and quantum transport modeling, the authors account for such major phenomena under experimental observation as the asymmetric impacts of adsorbed gases (e.g., oxygen) and chemical dopants (e.g., potassium). Notably, the research shows that contact geometry—e.g., electrode sharpness and orientation—plays a key role in optimizing device performance by concentrating the electric field and reducing the gate voltage needed for switching. These findings not only explain the nonintuitive operation mechanisms of CNT-FETs but also offer unambiguous design guidelines for maximizing future nanoscale transistor technologies.[15] 7]

Carbon nanotubes (CNTs), especially single-walled carbon nanotubes (SWCNTs), are at the forefront of nanoscale electronics due to their remarkable electrical, mechanical, and thermal properties. Among these, the ability of SWCNTs to support ballistic or near-ballistic charge transport over nano meter-length scales makes them particularly promising for high-performance applications, including field-effect transistors (FETs) and ultra-dense interconnects. Ballistic transport—where charge carriers move through the channel without scattering—is essential for achieving high current densities, rapid switching speeds, and low power dissipation. This study presents a simple yet effective fabrication method to create ultrashort SWCNT devices with channel lengths ranging from 10 to 50 nano meters, achieved without relying on complex tools like electron-beam lithography. By combining conventional photolithography with angle (shadow) evaporation, the authors demonstrate the large-scale realization of metallic and semiconducting SWCNT devices with minimal structural complexity. Notably, 10-nm-long metallic SWCNTs were shown to carry current densities up to 4×10^9 A/cm², far surpassing conventional metals, due to their quasi-ballistic transport properties. Similarly, 50-nm-long semiconducting SWCNT-FETs achieved high current levels and subthreshold characteristics indicative of near-ballistic performance. The work underscores the potential of SWCNTs for pushing the physical and performance limits of nanoelectronics, both as high-current interconnects and as molecular-scale transistors, while also offering a practical route for their scalable fabrication.[16] 8]

Carbon nanotubes (CNTs), especially semiconducting single-walled carbon nanotubes (SWCNTs), have been of great interest for potential use in next-generation nanoelectronics, such as high-speed transistors, single-electron memories, and sensitive chemical or biochemical sensors. Charge carrier mobility, a key figure of merit underlying their performance in these applications, determines both switching speed and detection sensitivity. Although earlier estimations of CNT mobility have been highly variable because of difficulties like short device lengths and non-Ohmic contacts, this research provides a solid estimation with ultra-long (>300 µm) SWCNT-based FETs. By maintaining channel resistance dominance over contact effects and working in the diffusive transport regime, the scientists were able to directly determine mobility values. Their measurements indicate a room-temperature field-effect mobility of as high as 79,000 $cm^2/V\cdot s$ and an intrinsic mobility of over 100,000 $cm^2/V\cdot s$—the highest to date at room temperature for any semiconductor. The results establish solidly the semiconducting CNTs as contenders for employment in ultra-fast, low-power, highly sensitive electronic devices.[17] 9]

Carbon Nanotube Field-Effect Transistors (CNTFETs) have come forward as next-generation nano electronic devices with high hopes due to their superior electrical properties and scalability. Of the numerous CNTFET architectures, Schottky Barrier CNTFETs (SB-CNTFETs)—where metal contacts are in Schottky barrier junctions with the semiconducting carbon nanotube channel—have received extensive research attention and experimental demonstrations. These transistors work through gate-regulated modulation of tunneling currents at the metal–nanotube interface and provide novel operating behaviors different from traditional silicon MOSFETs.It provides a quantitative atomistic study of the scaling properties and performance constraints of SB-CNTFETs by the self-consistent atomistic simulations based on non-equilibrium Green's function (NEGF) formalism. It targets primary design parameters such as gate oxide thickness and dielectric constant, nanotube diameter, Schottky barrier height, drain voltage, and channel length. Major findings indicate the pivotal role of ambipolar conduction in thin-oxide devices, the effect of nanotube diameter on leakage and drive currents, and the effect of source–drain tunneling on ultimate channel length scalability. The analysis states that, although CNTFETs provide competitive performance, they suffer from the same scaling limitations as traditional transistors owing to intrinsic quantum mechanical effects.[18] 10]

Carbon Nanotube Field-Effect Transistors (CNFETs) have emerged as promising alternatives to traditional silicon-based transistors, offering superior electrical performance at nanoscale dimensions. Unlike conventional MOSFETs, CNFETs often operate as Schottky barrier transistors, where current transport is dominated by tunneling through energy barriers at the metal–nanotube contacts. This fundamental distinction alters device behavior and impacts key performance parameters, including switching mechanisms and scaling rules. This study investigates the role of lateral scaling and gate field distribution in CNFETs using a novel device architecture featuring multiple, independently addressable gate segments. By decoupling the gate influence near the contacts from that in the central channel, the authors demonstrate a transition from contact-dominated Schottky barrier switching to bulk switching within the nanotube. Notably, measurements reveal that the current through the channel is independent of gate length, providing direct evidence of ballistic transport in semiconducting carbon nanotubes over distances of several hundred nano meters. These findings not only deepen our understanding of charge transport in CNFETs but also have significant implications for the design and scaling of future nano electronic devices.[19] 11]

In the last few years, sentiment analysis has grown from working with textual data to multimodal sources, including audio and video, which has allowed richer human emotion and opinion understanding. Multimodal sentiment analysis (MSA) uses multiple information streams to detect the subtle nuances that are potentially lost when only one modality is used. The combination of visual, text, and acoustic modalities has been found to perform better in sentiment identification, particularly for sophisticated and equivocal communication situations. Conventional sentiment analysis techniques tend to rely on hand-engineered features and shallow models, which do not generalize well across varied contexts. With the emergence of deep learning, specifically Transformer-based models such as BERT, XLNet, and RoBERTa, there has been a revolution in natural language processing and, by association, multimodal sentiment analysis. These models have demonstrated impressive ability to capture contextual relationships and semantic subtleties, thus improving the interpretability and accuracy of sentiment predictions. This work investigates the use of Transformer-based models in multimodal sentiment analysis on datasets like CMU-MOSEI, CMU-MOSI, and IEMOCAP. It seeks to compare the performance of different fusion methods and Transformer models in combining multimodal inputs to provide stable sentiment judgments. The outcomes add to the body of literature that calls for end-to-end deep learning models in multimodal applications and provide guidance on utilizing Transformer models in multimodal applications.[20] 12]

Carbon nanotube field-effect transistors (CNFETs) are potential candidates for next-generation nanoscale electronic devices because of their remarkable electrical, mechanical, and chemical characteristics. A lot of progress has been achieved in device performance since the first demonstration of semiconducting single-wall carbon nanotubes (SWNTs) as FETs, particularly through the application of thin gate dielectrics to lower operation voltages and successful demonstration of both p-type and n-type CNFETs. In spite of this advancement, a complete understanding of carrier transport mechanisms in CNFETs is still lacking. Traditional explanations in terms of bulk switching behavior are inadequate to account for some important experimental findings. This work fills this void by examining how internal electric fields—specifically those due to the gate and source-drain electrodes—affect carrier transport. By a set of experiments covering channel length variation, gate dielectric thickness variation, and material variation, the research proves that the subthreshold characteristics and current-voltage characteristics of CNFETs can be best explained by a Schottky barrier transistor model. This finding undermines conventional MOSFET analogies and offers a more realistic basis for understanding and engineering the electronic properties of carbon nanotube-based transistors.[21] 13]

The vision of utilizing individual molecules as electronic devices has captured researchers' imaginations for years with the potential to bring revolutionized miniaturization and integration capabilities. The strong candidates for molecular electronics among these include carbon nanotubes (CNTs) with their interesting electrical and structural characteristics to function as nanowire channels and semiconducting conduits. Whereas past demonstrations of molecular devices usually relied on cryogenic temperatures, enabling practical utilization calls for operation at room temperature. In the current research, the authors present the fabrication and electrical properties of a field-effect transistor (FET) made of one semiconducting single-wall carbon nanotube (SWCNT) material. The nanotube, spanning two metal electrodes and gated through a silicon substrate, shows definitive transistor-like switching at room temperature. The device switches between conducting and insulating states by adjusting the gate voltage, working similarly to conventional semiconductor transistors but at the molecular level. The measured electrical behavior is interpreted in terms of semiclassical band-bending models such as those used in standard semiconductor theory. In particular, the current-voltage characteristics demonstrate gate-controlled metallic to semiconducting switching behavior with conductance modulations by several orders of magnitude. These findings represent an important step towards the integration of molecular-scale components into future nano electronic circuits, with carbon nanotube-based transistors being strong contenders for room-temperature, high-speed applications.[22] 14]

Single-walled carbon nanotubes (SWNTs) have become building blocks in nanoscale electronics because of their outstanding electrical properties and one-dimensional nature. Knowledge of this electron-phonon interaction is important for both basic physics and future applications like high-speed, high-current electronic devices. At low electrical bias and room temperature, the dominant source of resistance in high-quality metallic SWNTs is supposed to be scattering by acoustic phonons, producing long electron mean free paths—usually of the order of micro meters. At higher biases, where electrons have enough energy to emit higher-energy phonons like optical or zone-boundary phonons, scattering becomes much stronger and may cut off the current, typically causing saturation at 20–25 µA. This work explores the nature of electron-phonon scattering in metal SWNTs through an investigation of how resistance depends on nanotube length at both low and high bias conditions. With a new experimental arrangement that utilizes an atomic force microscope (AFM) tip as a mobile electrode, the authors accurately measure resistance over a range of channel lengths. The data unveil a low-bias mean free path of about 1.6 µm, which agrees with acoustic phonon scattering, and a significantly reduced high-bias mean free path of about 10 nm, resulting from fast scattering from high-energy phonons. The data are corroborated by calculations of phonon emission rates and offer a complete picture of electron transport in metallic SWNTs across various operation regimes.[23] 15]

Conclusion

This work delivers a detailed exploration of electron-phonon scattering in metallic single-walled carbon nanotubes by correlating electrical resistance with nanotube length under both low and high bias conditions. It confirms that at room temperature and low bias, acoustic phonons dominate electron scattering, resulting in long mean free paths that support nearly ballistic transport. In contrast, at high bias, electrons acquire sufficient energy to emit optical and zone-boundary phonons, drastically shortening the mean free path and causing current saturation. The use of an AFM tip for spatially resolved resistance measurement enables a direct and reliable investigation of these effects. Theoretical calculations align closely with the experimental data, validating the models used to predict scattering rates. These findings provide critical insights into the transport properties of SWNTs and affirm their potential in future nanoelectronic applications that demand high-speed, low-power, and high-current performance. Moreover, understanding the mechanisms of phonon-limited transport will be essential for optimizing carbon nanotube-based device design and functionality.

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